HPE SmartMemory - DDR4 - module

16 GB - DIMM 288-pin - 2666 MHz / PC4-21300 - CL19 - 1.2 V - registered - ECC

Group	Memory Modules
Manufacturer	HPE
Manufacturer item no.	838089-B21
EAN/UPC	4514953966888

Description

HPE DDR4 SmartMemory delivers great performance, reliability, and efficiency. As workloads grow and data center trends such as server virtualization, cloud computing, and the use of large database applications increases the need for higher-capacity memory with greater uptime, the quality and reliability of DRAM become ever more important.

Main features

Product Description	HPE SmartMemory - DDR4 - module - 16 GB - DIMM 288-pin - 2666 MHz / PC4-21300 - registered
Product Type	Memory module
Capacity	16 GB
Memory Type	DDR4 SDRAM - DIMM 288-pin
Upgrade Type	System specific
Data Integrity Check	ECC
Speed	2666 MHz (PC4-21300)
Latency Timings	CL19 (19-19-19)
Features	Dual rank, registered
Voltage	1.2 V
OEM Manufacturer Equivalent Part Number	HP 838089-B21, HP 870840-001
Designed For	ProLiant DL325 Gen10, DL325 Gen10 Base, DL325 Gen10 Entry, DL325 Gen10 Performance, DL325 Gen10 SMB Solution, DL325 Gen10 Solution, DL385 Gen10, DL385 Gen10 Base, DL385 Gen10 Entry, DL385 Gen10 High-Performance, DL385 Gen10 Performance, DL385 Gen10 SMB, DL385 Gen10 Solution

Extended details

	General
Capacity	16 GB
Upgrade Type	System specific
OEM Manufacturer Equivalent Part Number	HP 838089-B21, HP 870840-001

	Memory
Type	DRAM memory module
Technology	DDR4 SDRAM
Form Factor	DIMM 288-pin
Speed	2666 MHz (PC4-21300)
Latency Timings	CL19 (19-19-19)
Data Integrity Check	ECC
Features	Dual rank, registered
Module Configuration	2048 x 72
Chips Organization	X8
Voltage	1.2 V
	Compatibility Information
Designed For	HPE ProLiant DL325 Gen10, DL325 Gen10 Base, DL325 Gen10 Entry, DL325 Gen10 Performance, DL325 Gen10 SMB Solution, DL325 Gen10 Solution, DL385 Gen10, DL385 Gen10 Base, DL385 Gen10 Entry, DL385 Gen10 High-Performance, DL385 Gen10 Performance, DL385 Gen10 SMB, DL385 Gen10 Solution

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